

# isc N-Channel Mosfet Transistor

## **BUZ11S2**

#### FEATURES

- Static Drain-Source On-Resistance
  - :  $R_{DS(on)} = 0.04 \Omega (Max)$
- SOA is Power Dissipation Limited
- · High input impedance
- High speed switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

#### DESCRITION



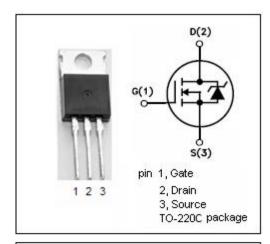
Designed for applications such as switching regulators, switching converters, motor drivers, relay drivers and drivers for high power bipolar switching transistors requiring high speed and low gate drive power.

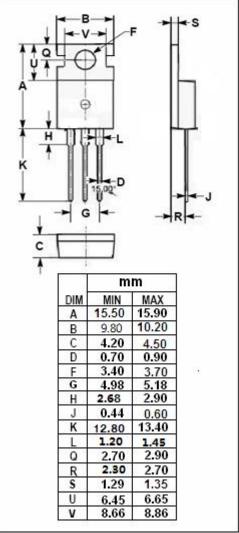
## • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	ARAMETER	VALUE	UNIT
V <sub>DSS</sub>	Drain-Source Voltage (V <sub>GS</sub> =0)	60	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub>	Drain Current-continuous@ TC=29℃	30	Α
I <sub>DM</sub>	Drain Current-Single Plused	120	Α
P <sub>tot</sub>	Total Dissipation@TC=25℃	75	W
Tj	Max. Operating Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.67	°C/W
R <sub>th j-a</sub>	Thermal Resistance,Junction to Ambient	75	°C/W







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## **ELECTRICAL CHARACTERISTICS**

T<sub>c</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0; I <sub>D</sub> =0.25mA	60			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; I <sub>D</sub> =1mA	2.1		4.0	V
V <sub>SD</sub>	Diode Forward On-voltage	I <sub>S</sub> = 60A ;V <sub>GS</sub> = 0			1.8	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> = 10V; I <sub>D</sub> = 19A			0.04	Ω
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>GS</sub> = ±20V;V <sub>DS</sub> = 0			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V; V <sub>GS</sub> = 0			1	μA
Gfs	Forward Transconductance	V <sub>DS</sub> = 25V; I <sub>D</sub> =19A	10			S
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>GS</sub> =10V;			25	
tr	Rise Time	I <sub>D</sub> =3A;			85	
t <sub>d(off)</sub>	Turn-off Delay Time	$V_{DD}$ =30V; R <sub>GS</sub> =50 Ω			160	ns
t <sub>f</sub>	Fall Time				110	

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